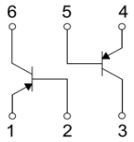
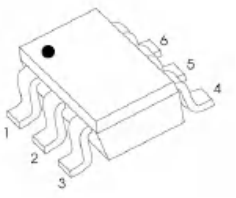
FEATURES

Epitaxial planar die construction
Ideal for low power amplification and switching





SOT-363

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

MAXIMUM RATINGS(T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-40	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.2	A
P_C	Collector Power Dissipation	0.2	W
$R_{\theta JA}$	Thermal Resistance. Junction to Ambient Air	625	℃/W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-10μA,I_E=0	-40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA,I_C=0	-5			V
Collector cut-off current	I_{CEX}	V_{CE}=-30V,$V_{EB(OFF)}$=-3V			-50	nA
Base cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-50	nA
DC current gain	$h_{FE(1)}$	V_{CE}=-1V,I_C=-0.1mA	60			
	$h_{FE(2)}$	V_{CE}=-1V,I_C=-1mA	80			
	$h_{FE(3)}$	V_{CE}=-1V,I_C=-10mA	100		300	
	$h_{FE(4)}$	V_{CE}=-1V,I_C=-50mA	60			
	$h_{FE(5)}$	V_{CE}=-1V,I_C=-100mA	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}$	I_C=-10mA,I_B=-1mA			-0.25	V
	$V_{CE(sat)2}$	I_C=-50mA,I_B=-5mA			-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)1}$	I_C=-10mA,I_B=-1mA	-0.65		-0.85	V
	$V_{BE(sat)2}$	I_C=-50mA,I_B=-5mA			-0.95	V
Transition frequency	f_T	V_{CE}=-20V,I_C=-10mA,f=100MHz	250			MHz
Collector output capacitance	C_{ob}	V_{CB}=-5V,I_E=0,f=1MHz			4.5	pF
Noise figure	NF	V_{CE}=-5V,I_c=-0.1mA,f=1KHz,R_g=1KΩ			4	dB
Delay time	t_d	V_{CC}=-3V, V_{BE}=0.5V			35	nS
Rise time	t_r	I_C=-10mA , I_{B1}=-I_{B2}=-1mA			35	nS
Storage time	t_S	V_{CC}=-3V, I_C=-10mA			225	nS
Fall time	t_f	I_{B1}=-I_{B2}=- 1mA			75	nS

RATING AND CHARACTERISTIC CURVES

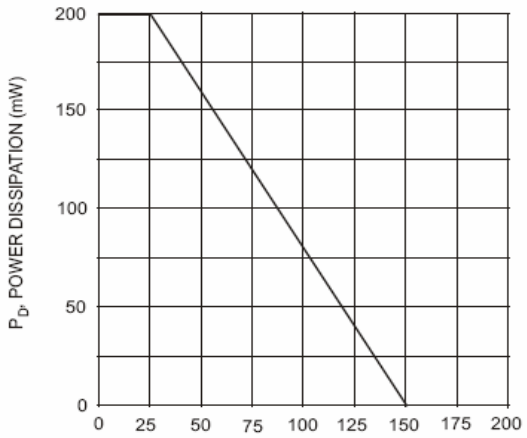


Fig. 1, Max Power Dissipation vs Ambient Temperature

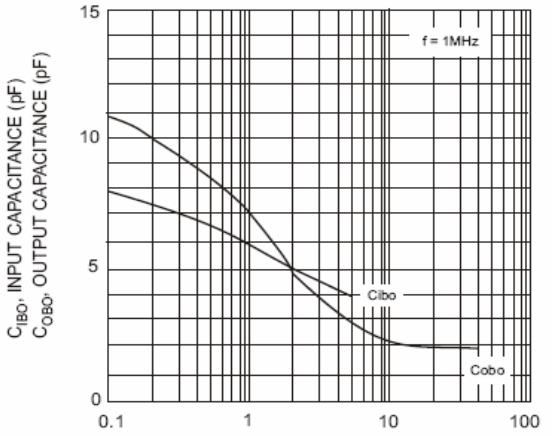


Fig. 2, Input and Output Capacitance vs. Collector-Base Voltage

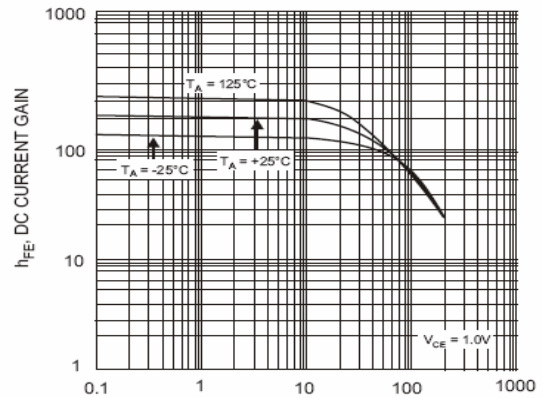


Fig. 3, Typical DC Current Gain vs Collector Current

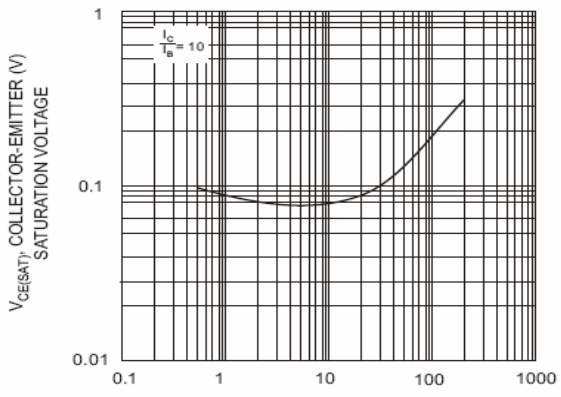


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

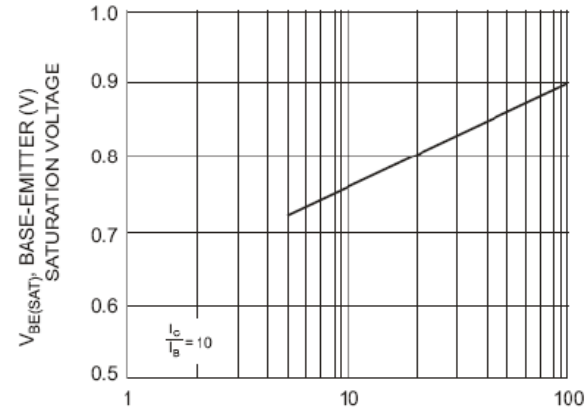
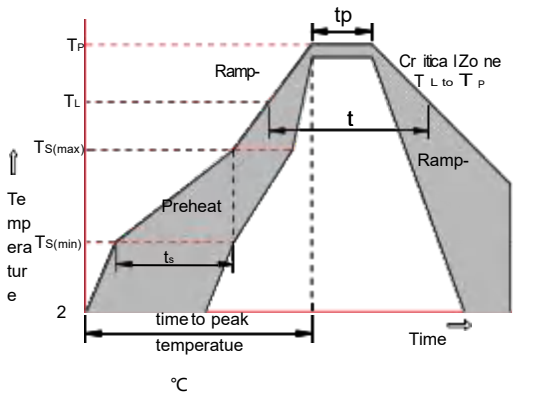


Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current

Soldering parameters

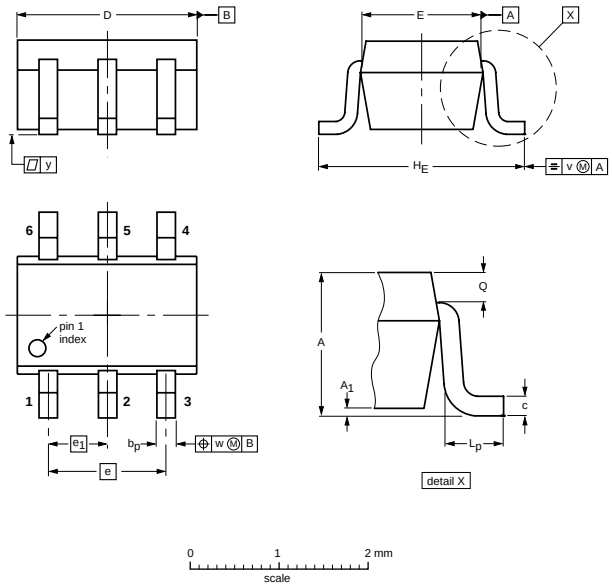
Reflow Condition		Pb-Free assembly (see as bellow)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150℃
	-Temperature Max($T_{s(max)}$)	+200℃
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3℃/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3℃/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217℃
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)℃
Time within 5℃ of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6℃/sec. Max
Time 25℃ to Peak Temp (T_P)		8 min. Max
Do not exceed		+260℃

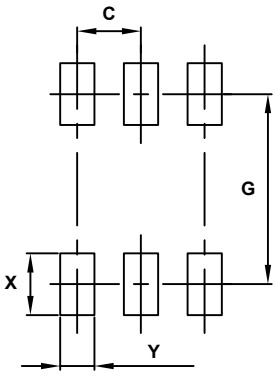
FIG5: Reflow condition



Package Dimensions & Suggested Pad Layout

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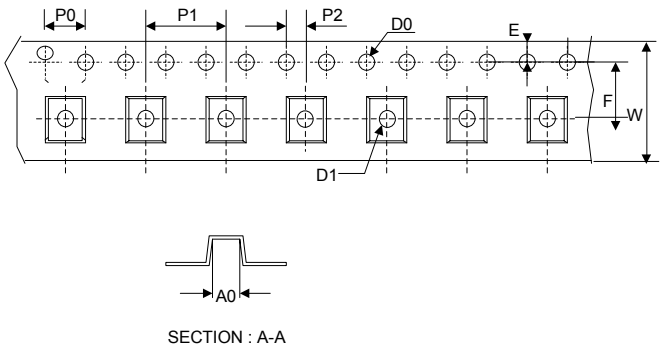
Dimensions	Value (in mm)
C	0.65
G	1.90
X	0.85
Y	0.40

DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

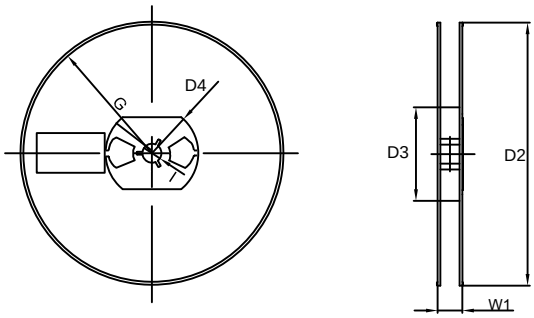
Tape & rell specification

Tape



Symbol	Dimension (mm)
P0	4.00±0.20
P1	4.00±0.20
P2	2.00±0.20
D0	1.55±0.20
D1	1.00±0.20
E	1.55±0.25
F	3.60±0.20
W	8.00±0.20
A0	3.00±0.20
B0	3.00±0.20
K0	1.30±0.20
T	0.20±0.20

7” Reel



D2	177.0±5.0
D3	55Min.
D4	R24.6±2.0
G	R82.0±2.0
I	13.0±2.0
W1	10.20±3.0

Quantity: 3000PCS